FAIRCHILD SEMICONDUCTOR®

June 2006

QFET®

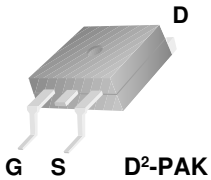
FQB16N25C/FQI16N25C
250V N-Channel MOSFET

Features

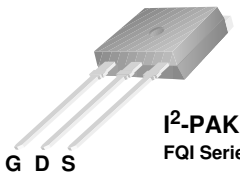
- 15.6A, 250V, $R_{DS(on)}$ = 0.27 Ω @V_{GS} = 10 V
- Low gate charge (typical 41nC)
- Low Crss (typical 68pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Description

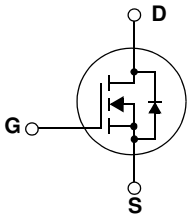
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supplies and motor controls.



D²-PAK
FQB Series



I²-PAK
FQI Series



Absolute Maximum Ratings

Symbol	Parameter		FQB16N25C / FQI16N25C	Units
V_{DSS}	Drain-Source Voltage		250	V
I_D	Drain Current - Continuous (T_C = 25°C)		15.6	A
	- Continuous (T_C = 100°C)		9.8	A
I_{DM}	Drain Current - Pulsed	(Note 1)	62.4	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	410	mJ
I_{AR}	Avalanche Current	(Note 1)	15.6	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	13.9	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P_D	Power Dissipation (T_A = 25°C)*		3.13	W
	Power Dissipation (T_C = 25°C)		139	W
	- Derate above 25°C		1.11	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8			

Thermal Characteristics

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQB16N25C	FQB16N25CTM	D2-PAK	330mm	24mm	800
FQI16N25C	FQI16N25CTU	I2-PAK	--	--	50

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	250	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.31	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 200 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 7.8A	--	0.22	0.27	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 7.8 A (Note 4)	--	10.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	830	1080	pF
C_{oss}	Output Capacitance		--	170	220	pF
C_{rss}	Reverse Transfer Capacitance		--	68	89	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125 V, I_D = 15.6A, R_G = 25 Ω	--	15	40	ns
t_r	Turn-On Rise Time		--	130	270	ns
$t_{d(off)}$	Turn-Off Delay Time		--	135	280	ns
t_f	Turn-Off Fall Time	(Note 4, 5)	--	105	220	ns
Q_g	Total Gate Charge	V_{DS} = 200 V, I_D = 15.6A, V_{GS} = 10 V	--	41	53.5	nC
Q_{gs}	Gate-Source Charge		--	5.6	--	nC
Q_{gd}	Gate-Drain Charge	(Note 4, 5)	--	22.7	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	15.6	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	62.4	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 15.6 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 15.6 A, dI_F / dt = 100 A/μs (Note 4)	--	260	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.47	--	μC

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 2.7mH, I_{AS} = 15.6A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 15.6A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics

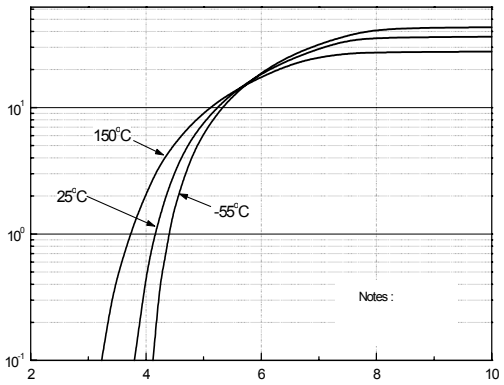


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature

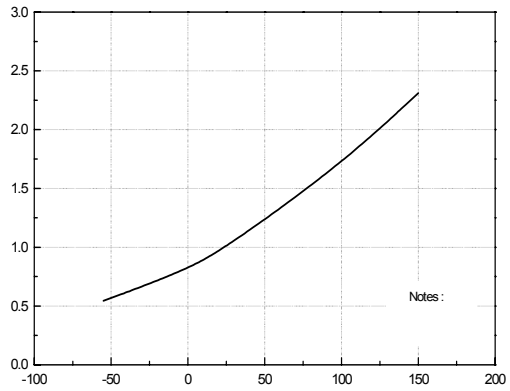
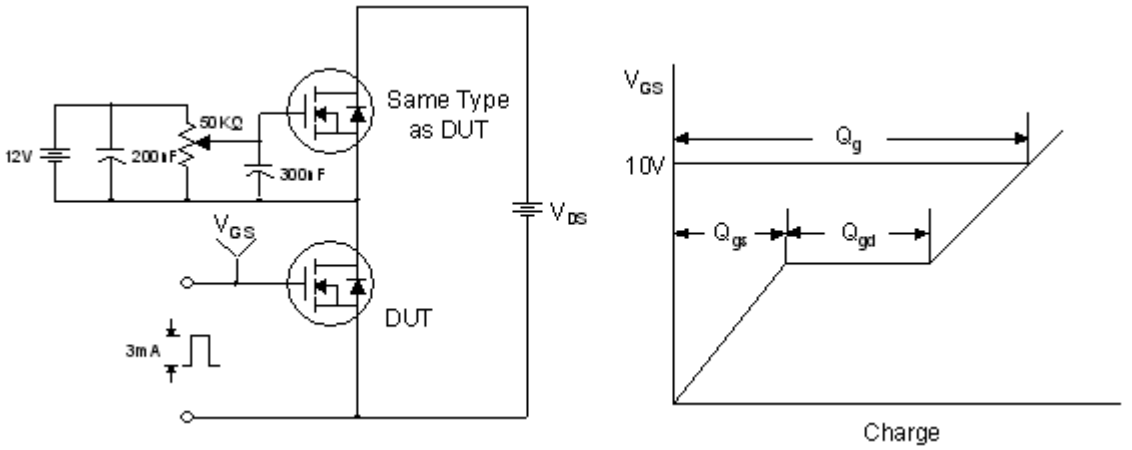


Figure 9. Maximum Safe Operating Area

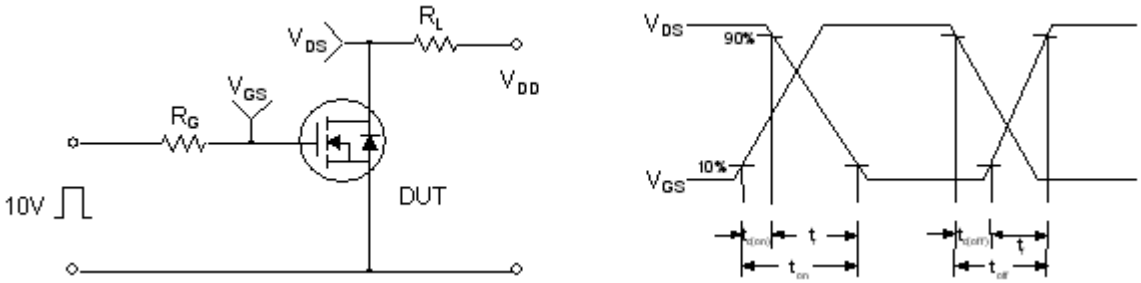
Figure 10. Maximum Drain Current vs. Case Temperature

Figure 11. Transient Thermal Response Curve

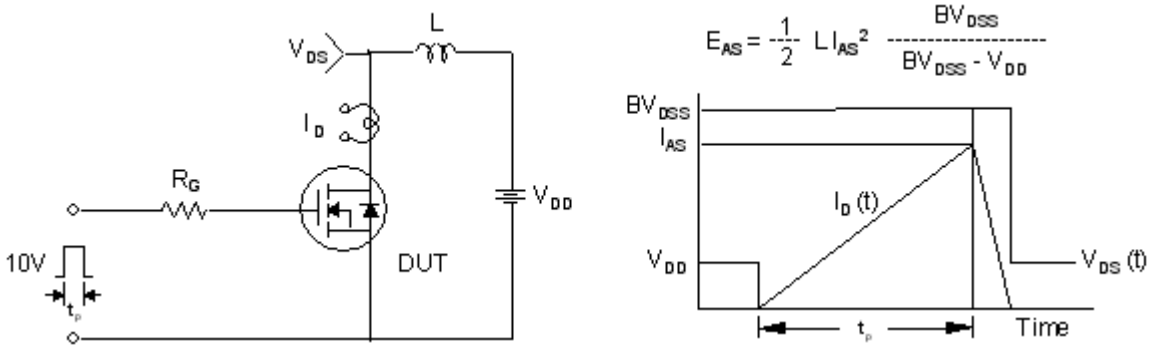
Gate Charge Test Circuit & Waveform



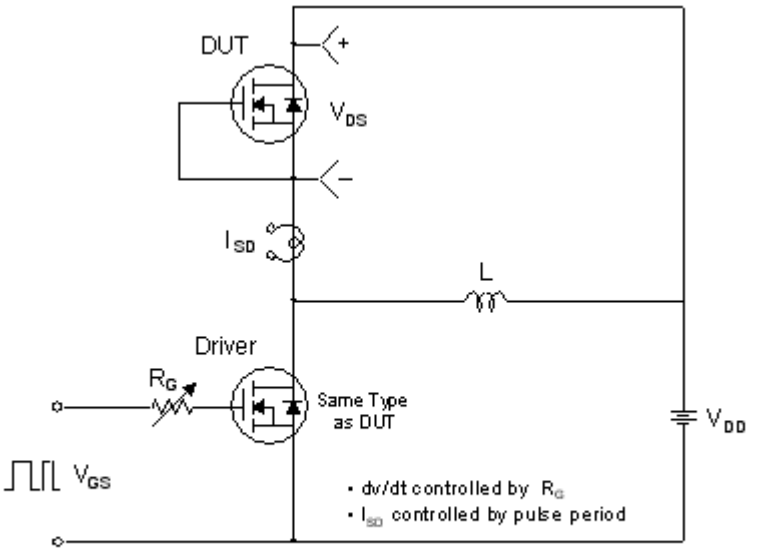
Resistive Switching Test Circuit & Waveforms

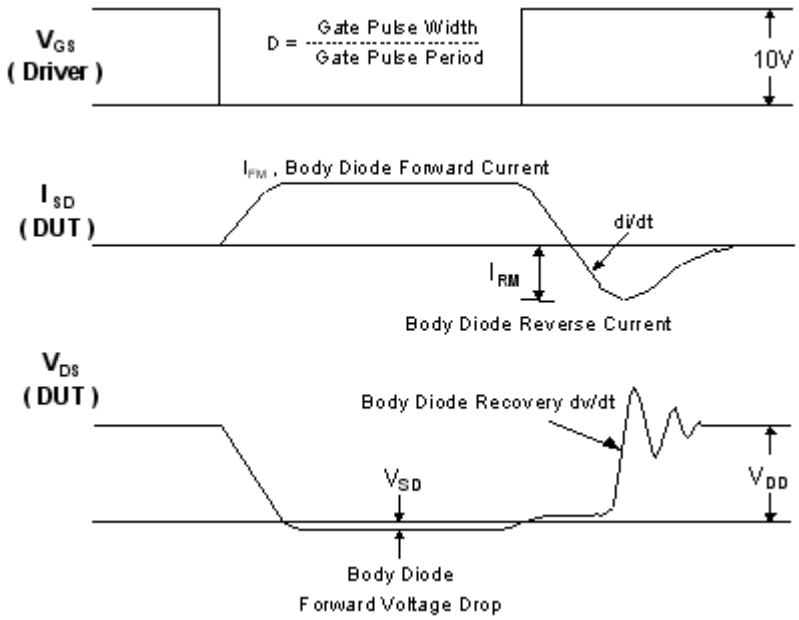


Unclamped Inductive Switching Test Circuit & Waveforms



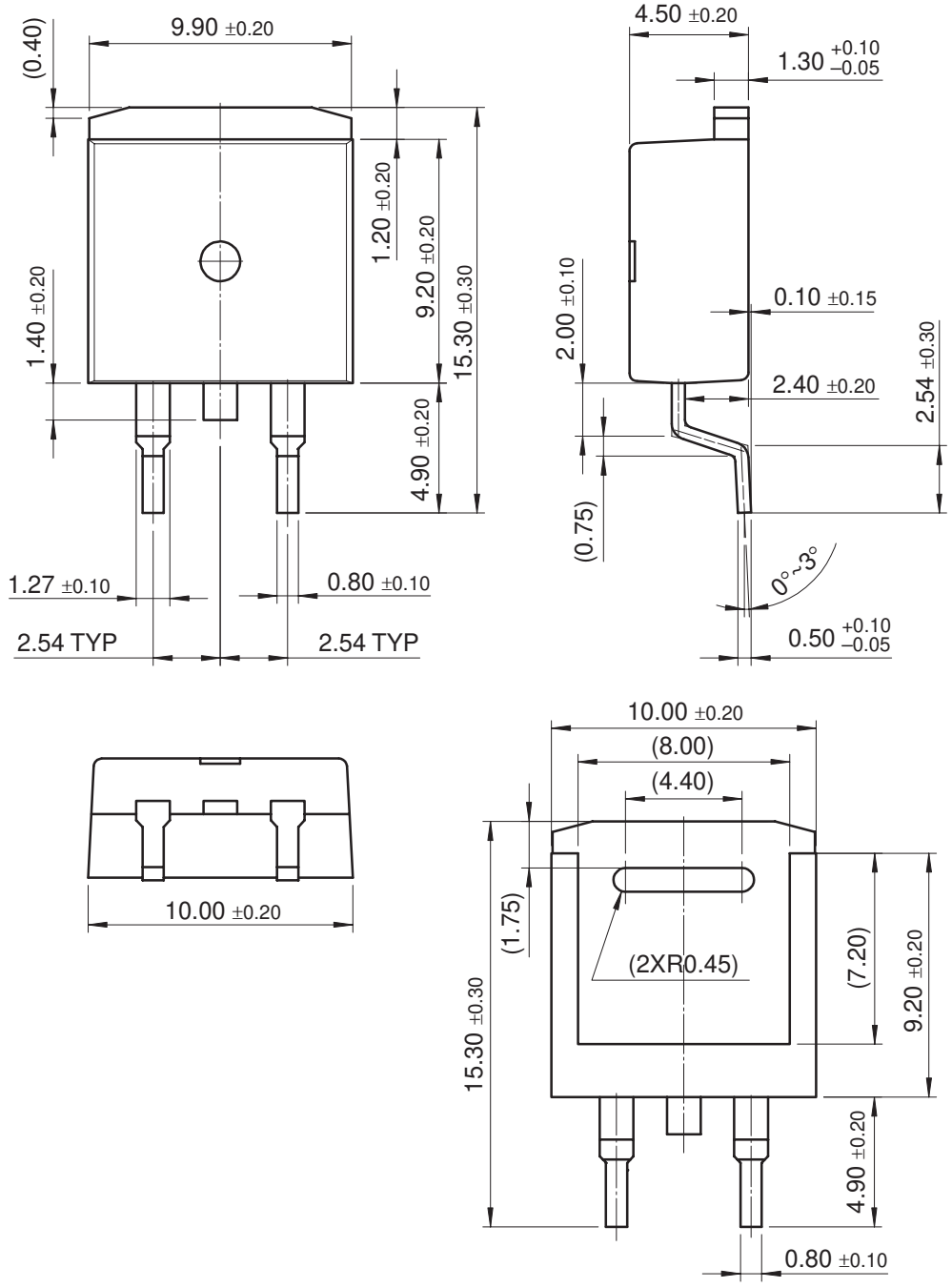
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

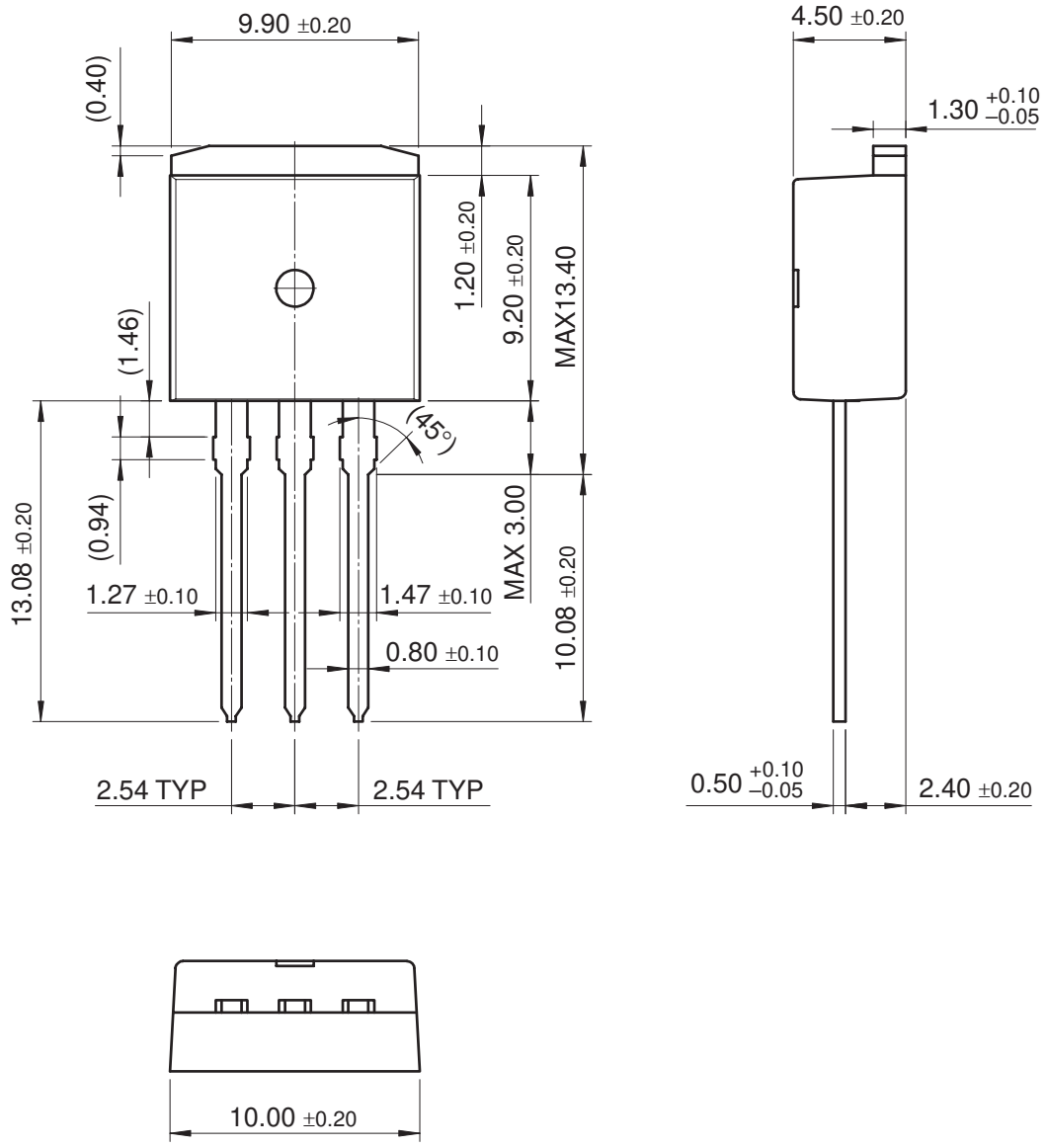
D²-PAK



Dimensions in Millimeters

Package Dimensions (Continued)

I²-PAK



Dimensions in Millimeters

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